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PATENT B  
10/10/02  
Smith

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Madhav Datta et al. Examiner: Erik Kielin  
Serial No.: 09/961,036 Group Art Unit: 2813  
Filed: September 21, 2001 Docket: 884.523US1  
Title: DUAL-STACK, BALL-LIMITING METALLURGY AND METHOD OF  
MAKING SAME

**ELECTION OF CLAIMS AND PRELIMINARY AMENDMENT**  
**UNDER 37 CFR § 1.115**

Commissioner for Patents  
Washington, D.C. 20231

In response to the Restriction Requirement mailed August 27, 2002, Applicant elects, with traverse, Group I (claims 17-19, 21, 23, and 25).

**IN THE CLAIMS**

Please amend the above-identified patent application as follows. Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of claim 17. The specific amendments to claim 17 is detailed in the following marked up claim.

17. (Amended) A process comprising:  
    forming a metallization;  
    forming a refractory metal first layer over the metallization;  
    forming a refractory metal second layer over the refractory metal first layer;  
    forming a refractory metal third layer above and on the refractory metal second layer, wherein the third refractory metal is substantially the same metal as the refractory metal first layer;  
    forming a refractory metal fourth layer above and on the refractory metal third layer, wherein the refractory metal fourth layer is substantially the same metal as the refractory metal second [first] layer; and  
    forming an electrically connective bump above the refractory metal fourth layer.

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